IN THE CLAIMS:

Please amend the claims as follows:

Claim 1 (Currently Amended): An etching mask ~~having a pass-through aperture for exposing only a surface to be etched~~ used for a plasma etching process of a thin film, comprising:

a pass-through aperture for exposing only a surface of the thin film to be etched;

a protruding periphery portion that protrudes at the periphery of the pass-through aperture, and

a ~~recessed~~ blocking portion enclosed by the protruding periphery portion for covering a surface of the thin film other than those that are to be etched.

Claim 2 (Original): The etching mask according to claim 1, wherein the pass-through aperture is covered by a mesh structure provided with a plurality of pass-through holes, each of the plurality of pass-through holes having an area that is smaller than the area of the pass-through aperture.

Claim 3 (Currently Amended): The etching mask according to claim 1, further comprising a blocking portion in a periphery portion of the etching mask at the side where the ~~recessed~~ blocking portion on the periphery of the pass-through aperture exists.

Claim 4 (Currently Amended): The etching mask according to claim 1, further comprising a reinforcement frame which is provided at the opposite side of the ~~recessed~~ blocking portion on the periphery of the pass-through aperture.

Claim 5 (Currently Amended): The etching mask according to claim 1, wherein the ~~recessed~~ blocking portion is made of conductive material.

Claim 6 (Currently Amended): The etching mask according to claim 1, wherein the ~~recessed~~ blocking portion is made of metal.

Claim 7 (Withdrawn): A thin film pattern forming method for forming a predetermined pattern on a thin film, comprising:

forming at least one thin film on a substrate; and

performing a dry etching process for placing a dry etching mask on the at least one thin film that has been formed and for applying an etching gas thereto;

wherein the dry etching mask is provided with a pass-through aperture for exposing only a surface to be etched, and is provided with a protruding periphery portion that protrudes at the periphery of the pass-through aperture, and a recessed portion enclosed by the protruding periphery portion.

Claim 8 (Withdrawn): The thin film pattern forming method according to claim 7, wherein the pass-through aperture is covered by a mesh structure provided with a plurality of

pass-through holes, each of the plurality of pass-through holes having a area that is smaller than the area of the pass-through aperture.

Claim 9 (Withdrawn): A method for manufacturing an organic electroluminescence element comprising at least one organic film that is placed between electrode layers and provides electroluminescence, comprising:

forming at least one organic film on a substrate; and

performing a dry etching process for placing a dry etching mask on the at least one organic film that has been formed and for applying an etching gas to at least one of the at least one organic film;

wherein the dry etching mask is provided with a pass-through aperture for exposing only a surface to be etched, and is provided with a protruding periphery portion that protrudes at the periphery of the pass-through aperture, and a recessed portion enclosed by the protruding periphery portion.

Claim 10 (Withdrawn): The organic electroluminescence element manufacturing method according to claim 9, wherein the pass-through aperture is covered by a mesh structure provided with a plurality of pass-through holes, each of the plurality of pass-through holes having an area that is smaller than the area of the pass-through aperture.

Claim 11 (Withdrawn): The organic electroluminescence element manufacturing method according to claim 9, wherein the etching gas includes an anisotropic etching gas.

Claim 12 (Withdrawn): The organic electroluminescence element manufacturing method according to claim 9, wherein the etching gas includes an anisotropic etching gas and an isotropic etching gas.

Claim 13 (Withdrawn): The organic electroluminescence element manufacturing method according to claim 9, wherein the etching gas includes an oxygen gas.

Claim 14 (Withdrawn): The organic electroluminescence element manufacturing method according to claim 9, wherein the etching gas includes an oxygen gas and an inert gas.

Claim 15 (Withdrawn): The organic electroluminescence element manufacturing method according to claim 9, wherein the step of performing a dry etching process performs etching of the organic film while connecting the substrate to a high frequency power source.

Claim 16 (Withdrawn): An organic electroluminescence element that is manufactured through an organic electroluminescence element manufacturing method having steps of forming at least one organic film on a substrate on which an electrode layer has been pre-laid; and performing a dry etching process for placing a dry etching mask on the at least one organic film that has been formed and for applying an etching gas thereto, comprising:

at least one electroluminescence film provided the electrode layer and any other subsequently formed electrode layer;

wherein the dry etching mask is provided with a pass-through aperture for exposing only a surface to be etched, and is provided with a protruding periphery portion that protrudes at the

periphery of the pass-through aperture, and a recessed portion enclosed by the protruding periphery portion.

Claim 17 (Withdrawn): The organic electroluminescence element according to claim 16, wherein the pass-through aperture is covered by a mesh structure provided with a plurality of pass-through holes, each of the plurality of pass-through holes having a area that is smaller than the area of the pass-through aperture.

Claim 18 (New): The etching mask according to claim 1, wherein the blocking portion is made of electrically conductive material.